AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of claims

1. (Currently Amended) A method for anodic bonding at least a portion of a MEMS device, the method comprising:

providing a first layer comprising a glass;

providing a ~~single material~~ first substrate comprising a polycrystalline material having an elastic modulus greater than about 300 gigaPascals;

causing a first surface of the first substrate to have an RMS surface roughness of greater than 0.001 μm and less than about 0.2 μm;

directly contacting the first surface of the first substrate to a surface of the first layer; and

applying a voltage between the first layer and the first substrate, through electrical contacts in direct contact with each of the first layer and the material having an elastic modulus greater than about 300 gigaPascals, to cause an effective anodic bond to form directly between the first layer and the first substrate. ~~a second surface of the package substantially opposite the first surface is exposed following the anodic bonding~~.

2. (Cancelled)

3. (Previously Presented) The method of claim 1, wherein the first substrate comprises silicon carbide.

4. (Cancelled)

5. (Original) The method of claim 1, wherein the glass comprises at least one of borosilicate glass and aluminosilicate glass.

6. (Previously Presented) The method of claim 1, wherein the glass is selected from the group consisting of borosilicate glass and aluminosilicate glass.

7. (Previously Presented) The method of claim 1, further comprising causing the first layer and the first substrate to have a temperature that does not exceed about 350 °C while applying the voltage.

8. (Original) The method of claim 1, wherein the RMS surface roughness is greater than 0.01 μm.

9. (Currently amended) The method of claim 8, wherein the RMS surface roughness is ~~greater~~ less than 0.15 μm.

10. (Original) The method of claim 1, wherein the RMS surface roughness is less than 0.1 μm.

11. (Original) The method of claim 1, wherein the voltage has a value in the range of 200 V to 1000 V.

12. (Previously Presented) The method of claim 1, further comprising causing the first surface of the first substrate to be hydrophobic.

13. (Previously Presented) The method of claim 1, further comprising:

providing a second substrate having an elastic modulus greater than about 300 gigaPascals;

causing a surface of the second substrate to have an RMS surface roughness of greater than 0.001 μm and less than 0.15 μm;

contacting the surface of the second substrate to a surface of the first layer; and

applying a voltage between the first layer and second substrate to cause an effective anodic bond to form between the first layer and second substrate.

14. (Previously Presented) The method of claim 13, further comprising thinning the first layer prior to contacting the surfaces of the first layer and second substrate.

15. (Previously Presented) The method of claim 14, wherein the thinning comprises causing the first layer to have a thickness of less than about 10.0 μm.

16. (Previously Presented) A device comprising a first layer and a first substrate bonded by the method of claim 1.

17. (Currently amended) A method for packaging a MEMS component, the method comprising:

providing a MEMS component comprising a glass layer having a surface and consisting essentially of at least one of a borosilicate glass and an aluminosilicate glass;

providing a ~~single material~~ device package comprising a material having an elastic modulus greater than about ~~150~~ 300 gigaPascals, formed from polycrystalline silicon carbide and having a first surface with an RMS surface roughness of greater than 0.001 μm and less than about 0.2[[15]] μm;

contacting the first surface of the package to the surface of the glass layer; and

causing the first surface of the package and the glass layer to have a temperature value that does not exceed about 350 °C while applying a voltage to form an effective bond between the MEMS component and the package, wherein the voltage is applied between the glass layer and the package through electrical contacts in direct contact with each of the glass layer and the material having an elastic modulus greater than about 300 gigaPascals ~~a second surface of the package substantially opposite the first surface is exposed following the anodic bonding~~.

18. (Cancelled)

19. (Previously Presented) The method of claim 1, wherein the first substrate is a device component.

20. (Previously Presented) The method of claim 1, wherein the first substrate is a device package.

21-23. (Cancelled)

24. (New) A method for anodic bonding at least a portion of a MEMS device, the method comprising:

providing a first layer comprising a glass;

providing a first substrate comprising a material having an elastic modulus greater than about 300 gigaPascals;

causing a first surface of the first substrate to have an RMS surface roughness of greater than 0.001 μm and less than about 0.2 μm;

directly contacting the first surface of the first substrate to a surface of the first layer; and

causing the first layer and the first substrate to have a temperature that does not exceed about 350 °C while applying a voltage between the first layer and the first substrate, through electrical contacts in direct contact with each of the first layer and the material having an elastic modulus greater than about 300 gigaPascals, to cause an effective anodic bond to form directly between the first layer and the first substrate.